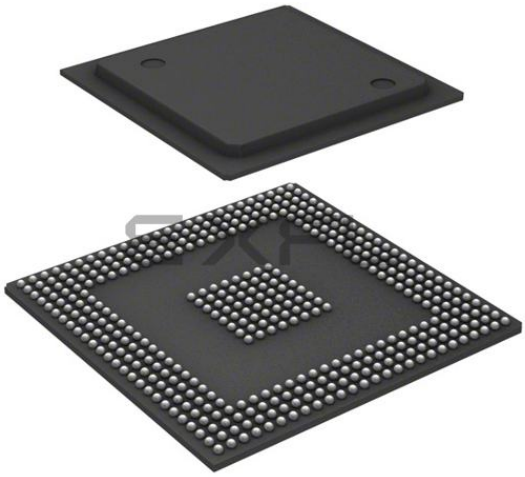

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

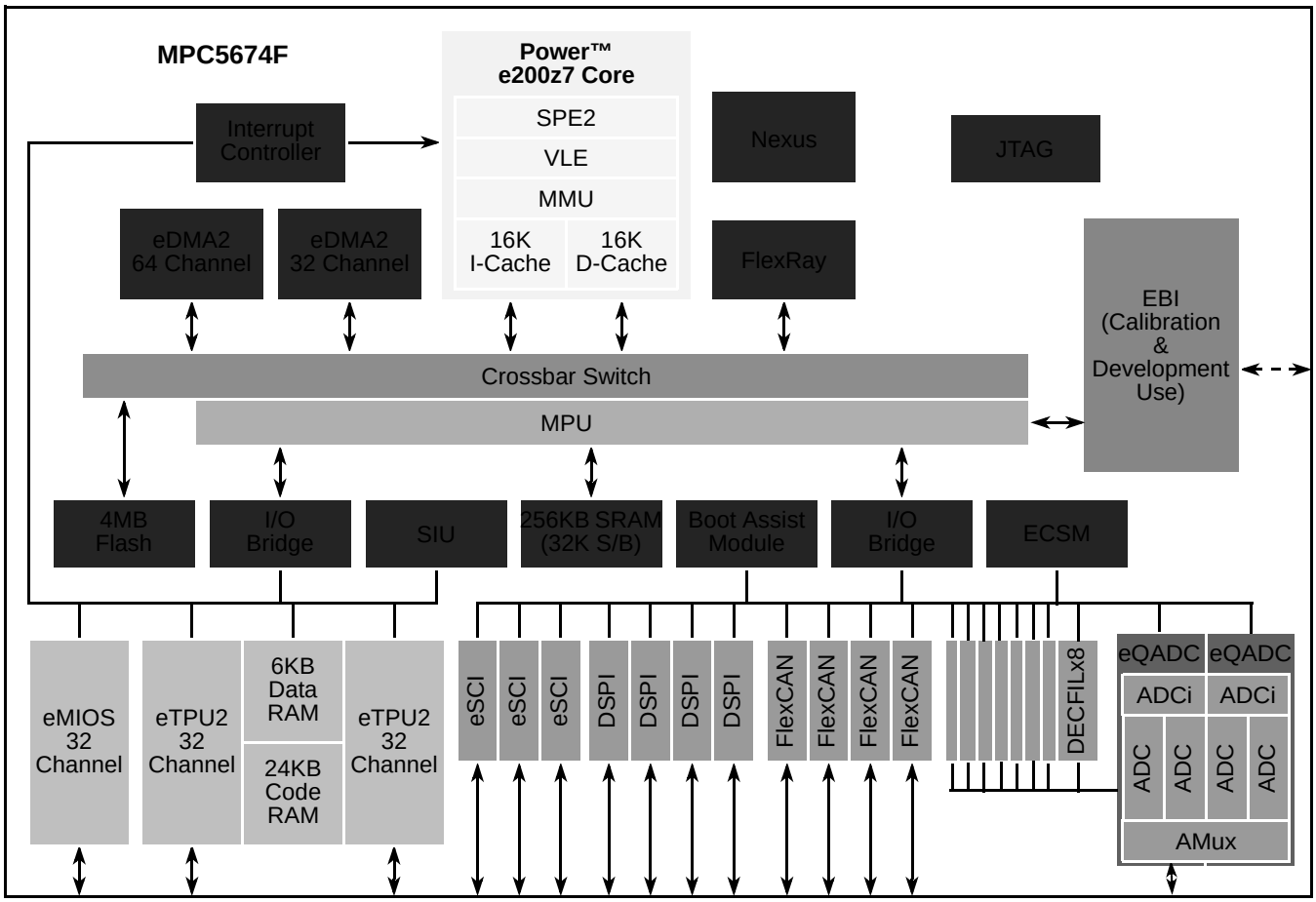
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z7
Core Size	32-Bit Single-Core
Speed	264MHz
Connectivity	CANbus, SCI, SPI
Peripherals	DMA, POR, PWM
Number of I/O	32
Program Memory Size	4MB (4M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.08V ~ 5.25V
Data Converters	A/D 64x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	416-BBGA
Supplier Device Package	416-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5674ff3mvr3r

2 MPC5674F Blocks

2.1 Block Diagram

Figure 2 shows a top-level block diagram of the MPC5674F device.



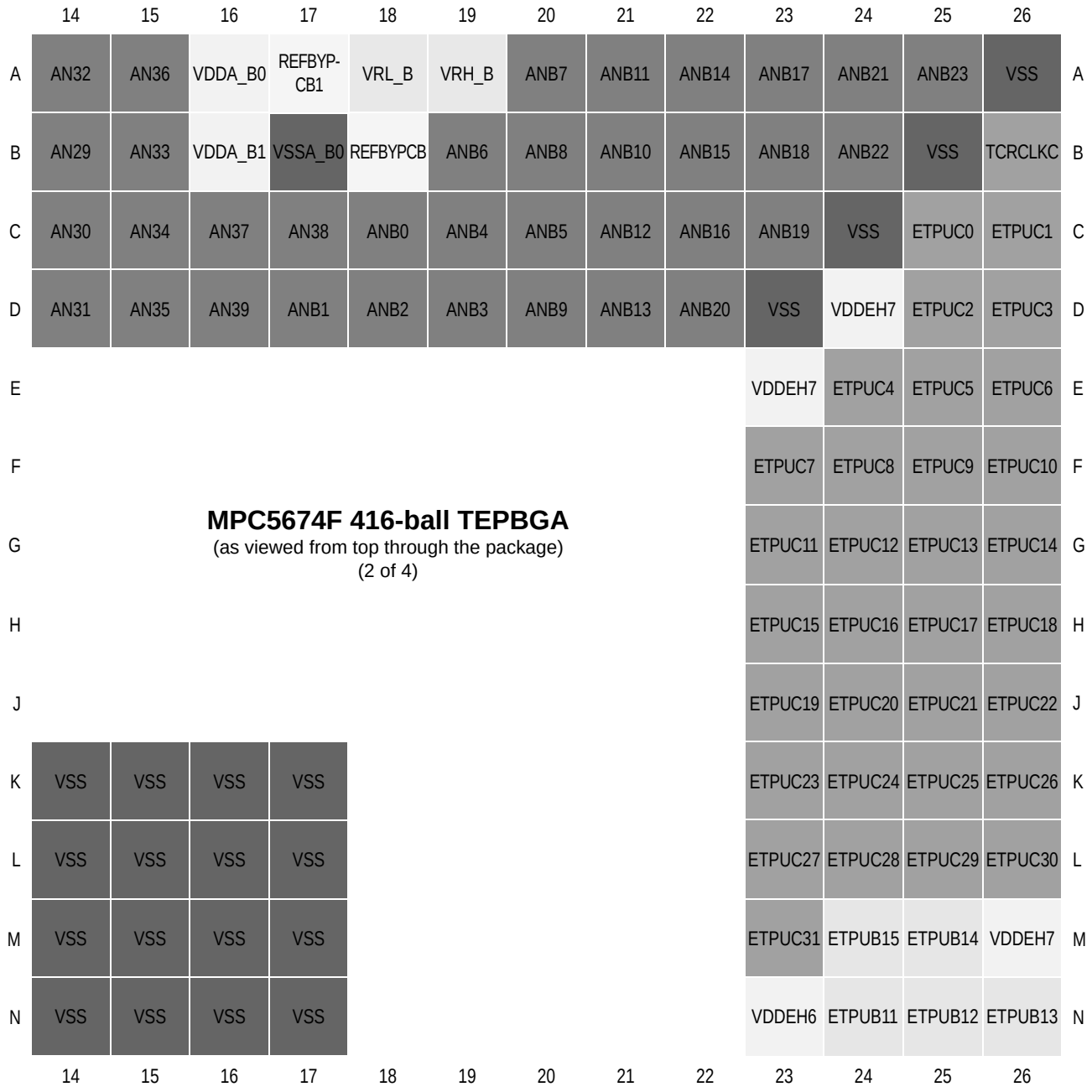
LEGEND

ADC	– Analog to digital convertor	**eSCI**	– Enhanced serial communications interface
ADCi	– ADC interface	**eTPU2**	– Enhanced time processing unit 2
AMux	– Analog multiplexer	**FlexCAN**	– Controller area network
DECFIL	– Decimation filter	**MMU**	– Memory management unit
DSPI	– Deserial/serial peripheral interface	**MPU**	– Memory protection unit
EBI	– External bus interface	**S/B**	– Stand-by
ECSM	– Error correction status module	**SIU**	– System integration unit
eDMA2	– Enhanced direct memory access	**SPE2**	– Signal processing engine 2
eMIOS	– Enhanced modular I/O system	**SRAM**	– General-purpose static RAM
eQADC	– Enhanced queued A/D converter module	**VLE**	– Variable length instruction encoding

Figure 2. Block Diagram

3 Pin Assignments

The figures in this section show the primary pin function. For the full signal properties and muxing table, see Appendix A, Signal Properties and Muxing.



	14	15	16	17	18	19	20	21	22	23	24	25	26	
A	AN32	AN36	VDDA_B0	REFBYP-CB1	VRL_B	VRH_B	ANB7	ANB11	ANB14	ANB17	ANB21	ANB23	VSS	A
B	AN29	AN33	VDDA_B1	VSSA_B0	REFBYPCB	ANB6	ANB8	ANB10	ANB15	ANB18	ANB22	VSS	TCRCLKC	B
C	AN30	AN34	AN37	AN38	ANB0	ANB4	ANB5	ANB12	ANB16	ANB19	VSS	ETPUC0	ETPUC1	C
D	AN31	AN35	AN39	ANB1	ANB2	ANB3	ANB9	ANB13	ANB20	VSS	VDDEH7	ETPUC2	ETPUC3	D
E										VDDEH7	ETPUC4	ETPUC5	ETPUC6	E
F										ETPUC7	ETPUC8	ETPUC9	ETPUC10	F
G										ETPUC11	ETPUC12	ETPUC13	ETPUC14	G
H										ETPUC15	ETPUC16	ETPUC17	ETPUC18	H
J										ETPUC19	ETPUC20	ETPUC21	ETPUC22	J
K	VSS	VSS	VSS	VSS						ETPUC23	ETPUC24	ETPUC25	ETPUC26	K
L	VSS	VSS	VSS	VSS						ETPUC27	ETPUC28	ETPUC29	ETPUC30	L
M	VSS	VSS	VSS	VSS						ETPUC31	ETPUB15	ETPUB14	VDDEH7	M
N	VSS	VSS	VSS	VSS						VDDEH6	ETPUB11	ETPUB12	ETPUB13	N
	14	15	16	17	18	19	20	21	22	23	24	25	26	

Figure 8. MPC5674F 416-ball TEPBGA (2 of 4)

6 Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature.

7 Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

4.2.1 General Notes for Specifications at Maximum Junction Temperature

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} * P_D) \quad \textit{Eqn. 1}$$

where:

T_A = ambient temperature for the package (^oC)

$R_{\theta JA}$ = junction to ambient thermal resistance ($^oC/W$)

P_D = power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the TEPBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA} \quad \textit{Eqn. 2}$$

where:

$R_{\theta JA}$ = junction to ambient thermal resistance ($^oC/W$)

$R_{\theta JC}$ = junction to case thermal resistance ($^oC/W$)

$R_{\theta CA}$ = case to ambient thermal resistance ($^oC/W$)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To determine the junction temperature of the device in the application when heat sinks are not used, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D) \quad \textit{Eqn. 3}$$

where:

T_T = thermocouple temperature on top of the package (^oC)

Ψ_{JT} = thermal characterization parameter ($^oC/W$)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the

4 “FM on” = FM depth of ±2%

5 K = 30 dBµV

Table 8. EMC Radiated Emissions Operating Behaviors: 516 BGA

Symbol	Description	Conditions	f_{OSC} f_{SYS}	Frequency band (MHz)	Level (max.)	Unit	Notes
V_{RE_TEM}	Radiated emissions, electric field and magnetic field	V_{DD} = 1.2 V V_{DDE} = 3.3 V V_{DDEH} = 5 V T_A = 25 °C 516 BGA EBI on CLK on FM off	40 MHz crystal 264 MHz (f_{EBI_CAL} = 66 MHz)	0.15–50	40	dBµV	1
				50–150	48		
				150–500	48		
				500–1000	47		
				IEC and SAE level	G[2]	—	1, 3
V_{RE_TEM}	Radiated emissions, electric field and magnetic field	V_{DD} = 1.2 V V_{DDE} = 3.3 V V_{DDEH} = 5 V T_A = 25 °C 516 BGA EBI on CLK on FM on[4]	40 MHz crystal 264 MHz (f_{EBI_CAL} = 66 MHz)	0.15–50	40	dBµV	1
				50–150	44		
				150–500	41		
				500–1000	36		
				IEC and SAE level	G[2]	—	1, 3

1 Determined according to IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method, and SAE Standard J1752-3, Measurement of Radiated Emissions from Integrated Circuits—TEM/Wideband TEM (GTEM) Cell Method.

2 G = 48 dBµV

3 Specified according to Annex D of IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method, and Appendix D of SAE Standard J1752-3, Measurement of Radiated Emissions from Integrated Circuits—TEM/Wideband TEM (GTEM) Cell Method.

4 “FM on” = FM depth of ±2%

4.4 ESD Characteristics

Table 9. ESD Ratings[1,2]

Spec	Characteristic	Symbol	Value	Unit
1	ESD for Human Body Model (HBM)	V_{HBM}	2000	V
2	ESD for Charged Device Model (CDM)	V_{CDM}	750 (corners) 500 (other)	V

1 All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

2 A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

4.5 PMC/POR/LVI Electrical Specifications

Note: For ADC internal resource measurements, see Table 21 in Section 4.9.1, “ADC Internal Resource Measurements.”

Table 11. PMC Electrical Specifications (continued)

ID	Name	Parameter	Min	Typ	Max	Unit
12c	—	LVD VDDREG Hysteresis (LDO3V / LDO5V mode)	—	30	—	mV
12d	$V_{LVDSTEPREG}$	Trimming step LVD VDDREG (LDO3V / LDO5V mode)	—	30	—	mV
13	V_{LVDREG}	Nominal rising LVD VDDREG (SMPS5V mode)	—	4.360	—	V
13a	—	Untrimmed LVD VDDREG variation before band gap trim **Note:** Rising VDDREG	V_{LVDREG} – 5%	V_{LVDREG}	V_{LVDREG} + 5%	V
13b	—	Trimmed LVD VDDREG variation after band gap trim **Note:** Rising VDDREG	V_{LVDREG} – 3%	V_{LVDREG}	V_{LVDREG} + 3%	V
13c	—	LVD VDDREG Hysteresis (SMPS5V mode)	—	50	—	mV
13d	$V_{LVDSTEPREG}$	Trimming step LVD VDDREG (SMPS5V mode)	—	50	—	mV
14	V_{LVDA}	Nominal rising LVD VDDA	—	4.60	—	V
14a	—	Untrimmed LVD VDDA variation before band gap trim	V_{LVDA} – 5%	V_{LVDA}	V_{LVDA} + 5%	V
14b	—	Trimmed LVD VDDA variation after band gap trim	V_{LVDA} – 3%	V_{LVDA}	V_{LVDA} + 3%	V
14c	—	LVD VDDA Hysteresis	—	150	—	mV
14d	$V_{LVDASTEP}$	Trimming step LVD VDDA	—	20	—	mV
15	—	SMPS regulator output resistance **Note:** Pulup to VDDREG when high, pulldown to VSSREG when low.	—	15	25	Ohm
16	—	SMPS regulator clock frequency (after reset)	1.0	1.5	2.4	MHz
17	—	SMPS regulator overshoot at start-up[2]	—	1.32	1.4	V
18	—	SMPS maximum output current	—	1.0	—	A
19	—	Voltage variation on current step[2] (20% to 80% of maximum current with 4 usec constant time)	—	—	0.1	V

1 VRC linear regulator is capable of sourcing a current up to 20 mA and sinking a current up to 500 uA. When using the recommended ballast transistor the maximum output current provided by the voltage regulator VRC/ballast to the VDD core voltage is up to 1A.

2 Parameter cannot be tested; this value is based on simulation and characterization.

4.7.3 LVDS Pad Specifications

LVDS pads are implemented to support the MSC (Microsecond Channel) protocol, which is an enhanced feature of the DSPI module.

Table 17. DSPI LVDS pad specification

#	Characteristic	Symbol	Condition	Min. Value	Typ. Value	Max. Value	Unit
Data Rate							
1	Data Frequency	$f_{LVDSCLK}$	—	—	50	—	MHz
Driver Specs							
2	Differential output voltage	V_{OD}	SRC=0b00 or 0b11	150	—	400	mV
			SRC=0b01	90	—	320	
			SRC=0b10	160	—	480	
3	Common mode voltage (LVDS), VOS	V_{OS}	—	1.06	1.2	1.39	V
4	Rise/Fall time	T_R/T_F	—	—	2	—	ns
5	Propagation delay (Low to High)	T_{PLH}	—	—	4	—	ns
6	Propagation delay (High to Low)	T_{PHL}	—	—	4	—	ns
7	Delay (H/L), sync Mode	t_{PDSYNC}	—	—	4	—	ns
8	Delay, Z to Normal (High/Low)	T_{DZ}	—	—	500	—	ns
9	Diff Skew ltphla-tplhbl or ltplhb-tphlal	T_{SKEW}	—	—	—	0.5	ns
Termination							
10	Trans. Line (differential Zo)	—	—	95	100	105	ohms
11	Temperature	—	—	–40	—	150	°C

4.8 Oscillator and FMPLL Electrical Characteristics

Table 18. FMPLL Electrical Specifications[1]

(V_{DDSYN} = 3.0 V to 3.6 V, V_{SS} = V_{SSSYN} = 0 V, T_A = T_L to T_H)

Spec	Characteristic	Symbol	Min	Max	Unit
1	PLL Reference Frequency Range[2] (Normal Mode) Crystal Reference (PLLCFG2 = 0b0) Crystal Reference (PLLCFG2 = 0b1) External Reference (PLLCFG2 = 0b0) External Reference (PLLCFG2 = 0b1)	 $f_{ref\_crystal}$ $f_{ref\_crystal}$ f_{ref_ext} f_{ref_ext}	 8 16 8 16	 20 40[3] 20 40	MHz
2	Loss of Reference Frequency[4]	f_{LOR}	100	1000	kHz
3	Self Clocked Mode Frequency[5]	f_{SCM}	4	16	MHz
4	PLL Lock Time[6]	t_{LPLL}	—	< 400	µs

Table 20. eQADC Conversion Specifications (Operating) (continued)

Spec	Characteristic	Symbol	Min	Max	Unit
9	Offset Error without Calibration	OFFNC	0[4]	100[4]	LSB
10	Offset Error with Calibration	OFFWC	–4[4]	4[4]	LSB
11	Full Scale Gain Error without Calibration	GAINNC	–120[4]	0[4]	LSB
12	Full Scale Gain Error with Calibration	GAINWC	–4[4,6]	4[4,6]	LSB
13	Non-Disruptive Input Injection Current [7, 8, 9, 10]	I_{INJ}	–3	3	mA
14	Incremental Error due to injection current[11, 12]	E_{INJ}	–4[4]	4[4]	Counts
15	TUE value at 8 MHz [13, 14] (with calibration)	TUE8	–4[4,6]	4[4,6]	Counts
16	TUE value at 16 MHz [13, 14] (with calibration)	TUE16	–8	8	Counts
17	Maximum differential voltage[15] (DANx+ - DANx-) or (DANx- - DANx+) PREGAIN set to 1X setting PREGAIN set to 2X setting PREGAIN set to 4X setting	 $DIFF_{max}$ $DIFF_{max2}$ $DIFF_{max4}$	 — — —	 $(V_{RH} – V_{RL})/2$ $(V_{RH} – V_{RL})/4$ $(V_{RH} - V_{RL})/8$	 V V V
18	Differential input Common mode voltage[15] (DANx- + DANx+)/2	$DIFF_{cmv}$	$(V_{RH} – V_{RL})/2$ – 5%	$(V_{RH} – V_{RL})/2$ + 5%	V

1 Stop mode recovery time is the time from the setting of either of the enable bits in the ADC Control Register to the time that the ADC is ready to perform conversions. Delay from power up to full accuracy = 8 ms.

2 At $V_{RH} – V_{RL}$ = 5.12 V, one count = 1.25 mV without using pregain.

3 INL and DNL are tested from V_{RL} + 50 LSB to V_{RH} – 50 LSB. The eQADC is guaranteed to be monotonic at 10 bit accuracy (12 bit resolution selected).

4 New design target. Actual specification will change following characterization. Margin for manufacturing has not been fully included.

5 At $V_{RH} – V_{RL}$ = 5.12 V, one LSB = 1.25 mV.

6 The value is valid at 8 MHz, it is ±8 counts at 16 Mhz.

7 Below disruptive current conditions, the channel being stressed has conversion values of $3FF for analog inputs greater than V_{RH} and $000 for values less than V_{RL}. Other channels are not affected by non-disruptive conditions.

8 Exceeding limit may cause conversion error on stressed channels and on unstressed channels. Transitions within the limit do not affect device reliability or cause permanent damage.

9 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values using $V_{POSCLAMP} = V_{DDA}$ + 0.5 V and $V_{NEGCLAMP}$ = –0.3 V, then use the larger of the calculated values.

10 Condition applies to two adjacent pins at injection limits.

11 Performance expected with production silicon.

12 All channels have same 10 kΩ < Rs < 100 kΩ Channel under test has Rs = 10 kΩ, I_{INJ}=I_{INJMAX},I_{INJMIN}.

13 The TUE specification is always less than the sum of the INL, DNL, offset, and gain errors due to cancelling errors.

14 TUE does not apply to differential conversions.

15 Voltages between VRL and VRH will not cause damage to the pins. However, they may not be converted accurately if the differential voltage is above the maximum differential voltage. In addition, conversion errors may occur if the common mode voltage of the differential signal violates the Differential Input common mode voltage specification.

Table 26. Flash EEPROM Module Life

Spec	Characteristic	Symbol	Min	Typical[1]	Unit
1	Number of program/erase cycles per block for 16 KB and 64 KB blocks over the operating temperature range (T_J)	P/E	100,000	—	cycles
2	Number of program/erase cycles per block for 128 KB and 256 KB blocks over the operating temperature range (T_J)	P/E	1,000	100,000	cycles
3	Minimum Data Retention at 85 °C ambient temperature[2] Blocks with 0–1,000 P/E cycles Blocks with 1,001–10,000 P/E cycles Blocks with 10,001–100,000 P/E cycles	Retention	 20 10 5	 — — —	years

1 Typical endurance is evaluated at 25 °C. Product qualification is performed to the minimum specification. For additional information on the Freescale definition of Typical Endurance, please refer to Engineering Bulletin EB619, *Typical Endurance for Nonvolatile Memory*.

2 Ambient temperature averaged over duration of application, not to exceed product operating temperature range.

Table 27 shows the Platform Flash Configuration Register 1 (PFCPR1) settings versus frequency of operation. Refer to the device reference manual for definitions of these bit fields.

Table 27. PFCPR1 Settings vs. Frequency of Operation[1]

Spec	Clock Mode	Maximum Frequency[2] (MHz)		APC = RWSC	WWSC	DPFEN[3]	IPFEN[3]	PFLIM[4]	BFEN[5]
		Core f_{sys}	Platform f_{platf}						
1	Enhanced	264 MHz[6]	132 MHz[6]	0b011	0b01	0b0 0b1	0b0 0b1	0b00 0b01 0b1x	0b0 0b1
2	Enhanced/ Full	200 MHz	100 MHz	0b010	0b01	0b0 0b1	0b0 0b1	0b00 0b01 0b1x	0b0 0b1
3	Legacy	132 MHz	132 MHz	0b100	0b01	0b0 0b1	0b0 0b1	0b00 0b01 0b1x	0b0 0b1
Default setting after reset:				0b111	0b11	0b00	0b00	0b00	0b0

1 Illegal combinations exist. Use entries from the same row in this table.

2 This is the nominal maximum frequency of operation: platform runs at $f_{sys}/2$ in Enhanced Mode .

3 For maximum flash performance, set to 0b1.

4 For maximum flash performance, set to 0b10.

5 For maximum flash performance, set to 0b1.

6 This is the nominal maximum frequency of operation in Enchanced Mode. Max speed is the maximum speed allowed including frequency modulation (FM). 270 MHz parts allow for 264 MHz system core clock(f_{sys}) + 2% FM and 132 Mhz platform clock (f_{platf})+ 2% FM.

Table 36. Bus Operation Timing [1] (continued)

Spec	Characteristic	Symbol	66 MHz (Ext. Bus Freq)[2 3]		Unit	Notes
			Min	Max		
7	Input Signal Valid to D_CLKOUT Posedge (Setup Time) D_ADD[9:30] D_DAT[0:15] D_RD_WR D_TA D_TS	t_{CIS}	5.0/4.5	—	ns	Input setup time selectable via SIU_ECCR[EBTS] bit: EBTS = 0; 5.0ns EBTS = 1; 4.5ns
8	D_CLKOUT Posedge to Input Signal Invalid (Hold Time) D_ADD[9:30] D_DAT[0:15] D_RD_WR D_TA D_TS	t_{CIH}	1.0	—	ns	
9	D_ALE Pulse Width	t_{APW}	6.5	—	ns	The timing is for Asynchronous external memory system.
10	D_ALE Negated to Address Invalid	t_{AAI}	2.0/1.0 [5]	—	ns	The timing is for Asynchronous external memory system. ALE is measured at 50% of VDDE.

1 EBI timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDE} = 3.0 V to 3.6 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H, and C_L = 30 pF with DSC = 0b10.

2 Speed is the nominal maximum frequency. Max speed is the maximum speed allowed including frequency modulation (FM). 270 MHz parts allow for 264 MHz system clock + 2% FM.

3 Depending on the internal bus speed, set the SIU_ECCR[EBDF] bits correctly not to exceed maximum external bus frequency. The maximum external bus frequency is 66 MHz.

4 Refer to Fast pad timing in Table 31 and Table 32.

5 ALE hold time spec is temperature dependant. 1.0 ns spec applies for temperature range -40 to 0 °C. 2.0 ns spec applies to temperatures > 0 °C. This spec has no dependency on SIU_ECCR[EBTS] bit.

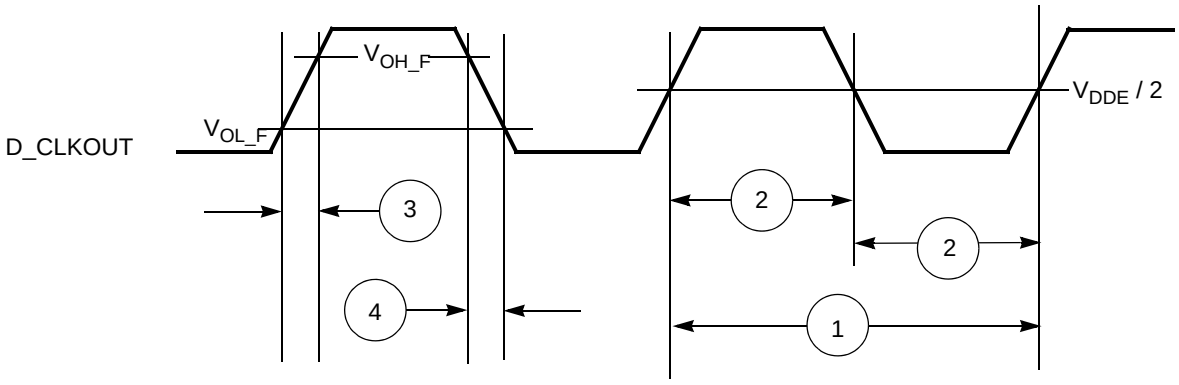


Figure 27. D_CLKOUT Timing

4.12.6 External Interrupt Timing (IRQ Pin)

Table 37. External Interrupt Timing[1]

Spec	Characteristic	Symbol	Min	Max	Unit
1	IRQ Pulse Width Low	t_{IPWL}	3	—	t_{cyc}[2]
2	IRQ Pulse Width High	t_{IPWH}	3	—	t_{cyc}[2]
3	IRQ Edge to Edge Time[3]	t_{ICYC}	6	—	t_{cyc}[2]

1 IRQ timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDEH} = 3.0 V to 5.5 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H.

2 See Notes on t_{cyc} on Figure 16 and Table 28 in Section 4.11.1 Clocking.

3 Applies when IRQ pins are configured for rising edge or falling edge events, but not both.

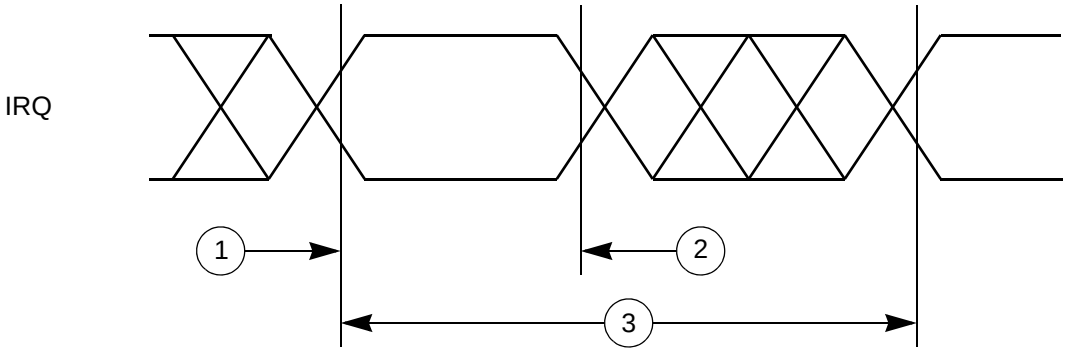


Figure 31. External Interrupt Timing

4.12.7 eTPU Timing

Table 38. eTPU Timing[1]

Spec	Characteristic	Symbol	Min	Max	Unit
1	eTPU Input Channel Pulse Width	t_{ICPW}	4	—	t_{cyc}[2]
2	eTPU Output Channel Pulse Width	t_{OCPW}	1[3]	—	t_{cyc}[2]

1 eTPU timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDEH} = 3.0 V to 5.5 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H, and C_L = 200 pF with SRC = 0b00.

2 See Notes on t_{cyc} on Figure 16 and Table 28 in Section 4.11.1 Clocking.

3 This specification does not include the rise and fall times. When calculating the minimum eTPU pulse width, include the rise and fall times defined in the slew rate control fields (SRC) of the pad configuration registers (PCR).

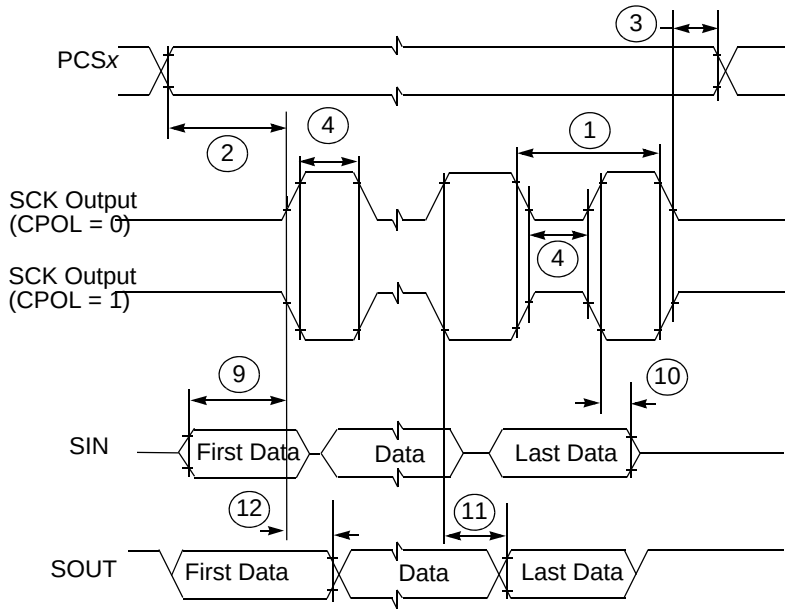


Figure 38. DSPI Modified Transfer Format Timing — Master, CPHA = 0

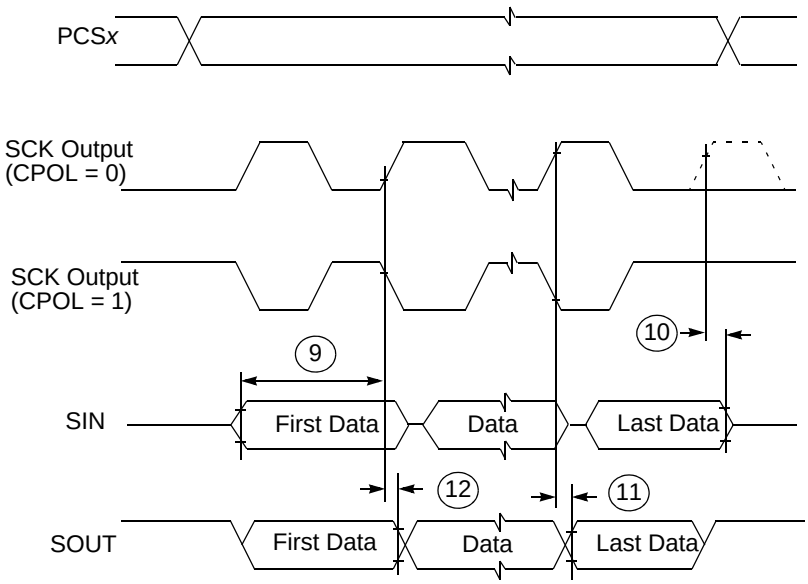


Figure 39. DSPI Modified Transfer Format Timing — Master, CPHA = 1

5.2 416-Pin Package

The package drawings of the 416-pin TEPBGA package are shown in Figure 45 and Figure 46.

Figure 45. 416 TEPBGA Package (1 of 2)

6 Product Documentation

This data sheet is labeled as a particular type: Product Preview, Advance Information, or Technical Data. Definitions of these types are available at: http://www.freescale.com.

The following documents are required for a complete description of the device and are necessary to design properly with the parts:

- *MPC5674F Microprocessor Reference Manual* (document number MPC5674FRM).

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
131	ETPUA17_PCSD2_ GPIO131	P	ETPUA17	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	G4	G3	G4
		A1	PCSD2	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO131	GPIO	I/O							
132	ETPUA18_PCSD3_ GPIO132	P	ETPUA18	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	—	G4	G5
		A1	PCSD3	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO132	GPIO	I/O							
133	ETPUA19_PCSD4_ GPIO133	P	ETPUA19	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	—	F1	F1
		A1	PCSD4	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO133	GPIO	I/O							
134	ETPUA20_IRQ8_ GPIO134	P	ETPUA20	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	E1	F2	F2
		A1	IRQ8	External interrupt request	I							
		A2	—	—	—							
		G	GPIO134	GPIO	I/O							
135	ETPUA21_IRQ9_ GPIO135	P	ETPUA21	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	C1	F3	F3
		A1	IRQ9	External interrupt request	I							
		A2	—	—	—							
		G	GPIO135	GPIO	I/O							
136	ETPUA22_IRQ10_ GPIO136	P	ETPUA22	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	E2	F4	F4
		A1	IRQ10	External interrupt request	I							
		A2	—	—	—							
		G	GPIO136	GPIO	I/O							

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
155	ETPUB8_ETPUB24_ GPIO155	P	ETPUB8	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	N21	P24	T24
		A1	ETPUB24	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO155	GPIO	I/O							
156	ETPUB9_ETPUB25_ GPIO156	P	ETPUB9	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	M22	P25	R22
		A1	ETPUB25	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO156	GPIO	I/O							
157	ETPUB10_ETPUB26_ GPIO157	P	ETPUB10	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	M20	P26	T25
		A1	ETPUB26	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO157	GPIO	I/O							
158	ETPUB11_ETPUB27_ GPIO158	P	ETPUB11	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	M21	N24	T26
		A1	ETPUB27	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO158	GPIO	I/O							
159	ETPUB12_ETPUB28_ GPIO159	P	ETPUB12	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	L19	N25	R23
		A1	ETPUB28	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO159	GPIO	I/O							
160	ETPUB13_ETPUB29_ GPIO160	P	ETPUB13	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	L20	N26	P22
		A1	ETPUB29	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO160	GPIO	I/O							

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
167	ETPUB20_ GPIO167	P	ETPUB20	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	—	V26	W24
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO167	GPIO	I/O							
168	ETPUB21_ GPIO168	P	ETPUB21	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	—	V25	V22
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO168	GPIO	I/O							
169	ETPUB22_ GPIO169	P	ETPUB22	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	—	V24	V23
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO169	GPIO	I/O							
170	ETPUB23_ GPIO170	P	ETPUB23	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	—	W26	U21
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO170	GPIO	I/O							
171	ETPUB24_ GPIO171	P	ETPUB24	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	—	W25	Y25
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO171	GPIO	I/O							
172	ETPUB25_ GPIO172	P	ETPUB25	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	—	W24	W21
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO172	GPIO	I/O							

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
—	AN27	P	AN27	eQADC A and B shared analog input	I	AE	V_{DDA_A0}	AN27	AN27	—	B13	B13
—	AN28	P	AN28	eQADC A and B shared analog input	I	AE	V_{DDA_A0}	AN28	AN28	—	A13	A13
—	AN29	P	AN29	eQADC A and B shared analog input	I	AE	V_{DDA_A0}	AN29	AN29	—	B14	A14
—	AN30	P	AN30	eQADC A and B shared analog input	I	AE	V_{DDA_B1}	AN30	AN30	—	C14	B14
—	AN31	P	AN31	eQADC A and B shared analog input	I	AE	V_{DDA_B1}	AN31	AN31	—	D14	C14
—	AN32	P	AN32	eQADC A and B shared analog input	I	AE	V_{DDA_B1}	AN32	AN32	—	A14	B15
—	AN33	P	AN33	eQADC A and B shared analog input	I	AE	V_{DDA_B0}	AN33	AN33	—	B15	D14
—	AN34	P	AN34	eQADC A and B shared analog input	I	AE	V_{DDA_B0}	AN34	AN34	—	C15	C15
—	AN35	P	AN35	eQADC A and B shared analog input	I	AE	V_{DDA_B0}	AN35	AN35	—	D15	D15
—	AN36	P	AN36	eQADC A and B shared analog input	I	AE	V_{DDA_B1}	AN36	AN36	—	A15	A15
—	AN37	P	AN37	eQADC A and B shared analog input	I	AE	V_{DDA_B0}	AN37	AN37	—	C16	C17
—	AN38	P	AN38	eQADC A and B shared analog input	I	AE	V_{DDA_B0}	AN38	AN38	—	C17	D16
—	AN39	P	AN39	eQADC A and B shared analog input	I	AE	V_{DDA_B0}	AN39	AN39	—	D16	C16
—	ANB0	P	ANB0	eQADC B analog input	I	AE/up-down	V_{DDA_B0}	ANB0	ANB0	B15	C18	C18
—	ANB1	P	ANB1	eQADC B analog input	I	AE/up-down	V_{DDA_B0}	ANB1	ANB1	B16	D17	D17
—	ANB2	P	ANB2	eQADC B analog input	I	AE/up-down	V_{DDA_B0}	ANB2	ANB2	A17	D18	D18
—	ANB3	P	ANB3	eQADC B analog input	I	AE/up-down	V_{DDA_B0}	ANB3	ANB3	A18	D19	D19
—	ANB4	P	ANB4	eQADC B analog input	I	AE/up-down	V_{DDA_B0}	ANB4	ANB4	B17	C19	B19
—	ANB5	P	ANB5	eQADC B analog input	I	AE/up-down	V_{DDA_B0}	ANB5	ANB5	B18	C20	A20
—	ANB6	P	ANB6	eQADC B analog input	I	AE/up-down	V_{DDA_B0}	ANB6	ANB6	A19	B19	C20
—	ANB7	P	ANB7	eQADC B analog input	I	AE/up-down	V_{DDA_B0}	ANB7	ANB7	A20	A20	C19
—	ANB8	P	ANB8	eQADC B analog input	I	AE	V_{DDA_B0}	ANB8	ANB8	D13	B20	B20

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
—	ANB9	P	ANB9	eQADC B analog input	I	AE	V_{DDA_B0}	ANB9	ANB9	C14	D20	A21
—	ANB10	P	ANB10	eQADC B analog input	I	AE	V_{DDA_B0}	ANB10	ANB10	C13	B21	B21
—	ANB11	P	ANB11	eQADC B analog input	I	AE	V_{DDA_B0}	ANB11	ANB11	C15	A21	C21
—	ANB12	P	ANB12	eQADC B analog input	I	AE	V_{DDA_B0}	ANB12	ANB12	C16	C21	A22
—	ANB13	P	ANB13	eQADC B analog input	I	AE	V_{DDA_B0}	ANB13	ANB13	D14	D21	B22
—	ANB14	P	ANB14	eQADC B analog input	I	AE	V_{DDA_B0}	ANB14	ANB14	C17	A22	D20
—	ANB15	P	ANB15	eQADC B analog input	I	AE	V_{DDA_B0}	ANB15	ANB15	D15	B22	C22
—	ANB16	P	ANB16	eQADC B analog input	I	AE	V_{DDA_B0}	ANB16	ANB16	C18	C22	D21
—	ANB17	P	ANB17	eQADC B analog input	I	AE	V_{DDA_B0}	ANB17	ANB17	D16	A23	D22
—	ANB18	P	ANB18	eQADC B analog input	I	AE	V_{DDA_B0}	ANB18	ANB18	D17	B23	A23
—	ANB19	P	ANB19	eQADC B analog input	I	AE	V_{DDA_B0}	ANB19	ANB19	B19	C23	B23
—	ANB20	P	ANB20	eQADC B analog input	I	AE	V_{DDA_B0}	ANB20	ANB20	C19	D22	C23
—	ANB21	P	ANB21	eQADC B analog input	I	AE	V_{DDA_B0}	ANB21	ANB21	D18	A24	A24
—	ANB22	P	ANB22	eQADC B analog input	I	AE	V_{DDA_B0}	ANB22	ANB22	A21	B24	B24
—	ANB23	P	ANB23	eQADC B analog input	I	AE	V_{DDA_B0}	ANB23	ANB23	B20	A25	E20
—	VRH_A	P	VRH_A	ADC A Voltage reference high	I	VDDINT	V_{RH_A}	VRH_A	VRH_A	A10	A12	A12
—	VRL_A	P	VRL_A	ADC A Voltage reference low	I	VSSINT	V_{RL_A}	VRL_A	VRL_A	A11	A11	A11
—	VRH_B	P	VRH_B	ADC B Voltage reference high	I	VDDINT	V_{RH_B}	VRH_B	VRH_B	A16	A19	A19
—	VRL_B	P	VRL_B	ADC B Voltage reference low	I	VSSINT	V_{RL_B}	VRL_B	VRL_B	A15	A18	A18
—	REFBYPCB	P	REFBYPCB	ADC B Reference bypass capacitor	I	AE	V_{DDA_B0}	REFBYPCB	REFBYPCB	B12	B18	B18
—	REFBYPCA	P	REFBYPCA	ADC A Reference bypass capacitor	I	AE	V_{DDA_A1}	REFBYPCA	REFBYPCA	B11	B11	B11
—	VDDA_A0	P	VDDA_A	Internal logic supply input	I	VDDE	V_{DDA_A0}	VDDA_A0	VDDA_A0	A9	A9	A9
—	VDDA_A1	P	VDDA_A	Internal logic supply input	I	VDDE	V_{DDA_A1}	VDDA_A1	VDDA_A1	B9	B9	B9
—	REFBYPCA1	P	REFBYPCA1	ADC A Reference bypass capacitor	I	AE	V_{DDA_A1}	REFBYPCA1	REFBYPCA1	A12	A10	A10
—	VSSA_A1	P	VSSA_A	Ground	I	VSSE	V_{SSA_A1}	VSSA_A1	VSSA_A1	B10	B10	B10
—	VDDA_B0	P	VDDA_B	Internal logic supply input	I	VDDE	V_{DDA_B0}	VDDA_B0	VDDA_B0	A13	A16	A16
—	VDDA_B1	P	VDDA_B	Internal logic supply input	I	VDDE	V_{DDA_B1}	VDDA_B1	VDDA_B1	B13	B16	B16

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
102	SCKB_ GPIO102	P	SCKB	DSPI B clock	I/O	MH	V_{DDEH3}	—/Up	—/Up	Y8	AE8	AC8
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO102	GPIO	I/O							
103	SINB_ GPIO103	P	SINB	DSPI B data input	I	MH	V_{DDEH3}	—/Up	—/Up	AA8	AE9	AB9
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO103	GPIO	I/O							
104	SOUTB_ GPIO104	P	SOUTB	DSPI B data output	O	MH	V_{DDEH3}	—/Up	—/Up	AB8	AF9	AA10
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO104	GPIO	I/O							
105	PCSB0_PCSD2_ GPIO105	P	PCSB0	DSPI B peripheral chip select	I/O	MH	V_{DDEH3}	—/Up	—/Up	Y9	AD9	AF8
		A1	PCSD2	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO105	GPIO	I/O							
106	PCSB1_PCSD0_ GPIO106	P	PCSB1	DSPI B peripheral chip select	O	MH	V_{DDEH3}	—/Up	—/Up	—	AC9	AE8
		A1	PCSD0	DSPI D peripheral chip select	I/O							
		A2	—	—	—							
		G	GPIO106	GPIO	I/O							
107	PCSB2_SOUTC_ GPIO107	P	PCSB2	DSPI B peripheral chip select	O	MH	V_{DDEH3}	—/Up	—/Up	W7	AF8	AD8
		A1	SOUTC	DSPI C data output	O							
		A2	—	—	—							
		G	GPIO107	GPIO	I/O							

Table 43. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
283	D_ADD_DAT5_ GPIO283	P	D_ADD_DAT5	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	M25
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO283	GPIO	I/O							
284	D_ADD_DAT6_ GPIO284	P	D_ADD_DAT6	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	N22
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO284	GPIO	I/O							
285	D_ADD_DAT7_ GPIO285	P	D_ADD_DAT7	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	M24
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO285	GPIO	I/O							
286	D_ADD_DAT8_ GPIO286	P	D_ADD_DAT8	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	M23
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO286	GPIO	I/O							
287	D_ADD_DAT9_ GPIO287	P	D_ADD_DAT9	EBI data only in non-mux mode. Address and data in mux mode.	I/O	F	V_{DDE10}	—/Up	—/Up	—	—	M22
		A1	—	—	—							
		A2	—	—	—							
		G	GPIO287	GPIO	I/O							